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(21)Application number: 2001-148194 (71)Applicant: DAINIPPON SCREEN MFG CO LTD

(22)Date of filing: 17.05.2001 (72)Inventor: MIZOBATA IKUO

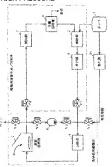
MURAOKA YUSUKE SAITO KIMITSUGU KITAKADO RYUJI INOUE YOICHI SAKASHITA YOSHIHIKO WATANABE KATSUMITSU YAMAGATA MASAHIRO

KOBE STEEL LTD

(54) APPARATUS AND METHOD FOR TREATING UNDER HIGH PRESSURE

PROBLEM TO BE SOLVED: To provide an apparatus and a method for treating a substrate under high pressure, in which the substrate can be treated by using a pure processing fluid so that the atmospheric component intruded into a treating tank when the substrate is placed is not made to flow in a fluid producing/recovering system.

SOLUTION: Valves V1, V2, V3, V4 and V6 are closed and only a valve V5 is opened when the door of a substrate cleaning tank 5 is opened for placing the substrate so that gaseous carbon dioxide is supplied to the tank 5 and the tank 5 is purged for preventing the atmospheric component from intruding into the tank 5. Next, the door of the tank 5 is closed and the valve V6 is opened at the same time to form a venting line of the tank 5 so that the gas existing in the tank 5 and its surrounding pipes is pushed out to the atmosphere by the supplied gaseous carbon dioxide and the tank 5 is purged so that the atmospheric component to intrude



into the tank 5 and its surrounding pipes by some rare accident does not stay behind. Then, the substrate is cleaned by using supercritical carbon dioxide.